



SOT-523 Plastic-Encapsulated Diode

DAP222 SWITCHING DIODE

FEATURES:

Power dissipation

$$P_D: 150 \text{ mW (Tamb=25°C)}$$

Collector current

$$I_F: 100 \text{ mA}$$

Collector-base voltage

$$V_R: 80 \text{ V}$$

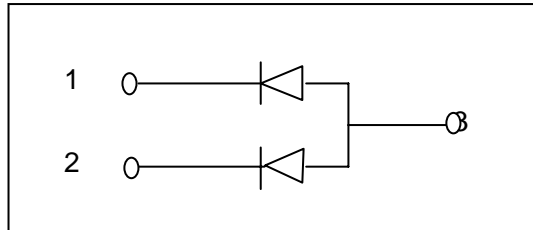
Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

SOT-523



CIRCUIT:



MARKING: P

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu\text{A}$	80		V
Reverse voltage leakage current	I_R	$V_R = 70\text{V}$		0.1	μA
Forward voltage	V_F	$I_F = 100\text{mA}$		1.2	V
Diode capacitance	C_D	$V_R = 6\text{V}, f = 1\text{MHz}$		3.5	pF
Reverse recovery time	t_{rr}	$V_R = 6\text{V}, I_F = 5\text{mA}$		4	ns